

## 2SC536 TRANSISTOR (NPN)

## **FEATURES**

Power dissipation

P<sub>CM</sub>: 400 mW (Tamb=25°C)

Collector current

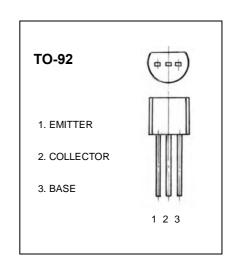
100 mA  $I_{CM}$ :

Collector-base voltage

 $V_{(BR)CBO}$ : 40 V

Operating and storage junction temperature range

T<sub>J</sub>, T<sub>stg</sub>: -55℃ to +150℃



## ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	Ic=100μA, I <sub>E</sub> =0	40			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	Ic=1mA, I <sub>B</sub> =0	30			V
Emitter-Base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =100μA, I <sub>C</sub> =0	5			V
Collector cut-off current	I <sub>CBO</sub>	$V_{CB}$ =35V, $I_E$ =0			1	μΑ
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =4V, I <sub>C</sub> =0			1	μA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =6V, I <sub>C</sub> =1mA	60		960	
Collector-emitter saturation voltage	V <sub>CE</sub> (sat)	I <sub>C</sub> =50mA, I <sub>B</sub> =5mA			0.5	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =6V, I <sub>C</sub> =1mA		100		MHz
Collector output capacitance	Cob	V <sub>CE</sub> =6V, f=1MHz		3.5		pF

## CLASSIFICATION OF hFE

Rank	D	E	F	G	Н
Range	60-120	100-200	160-320	280-560	480-960